

## KA2803B

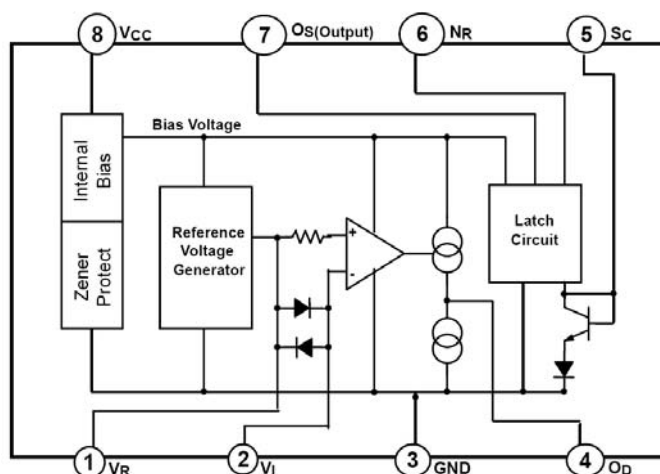


Figure 1. Block Diagram

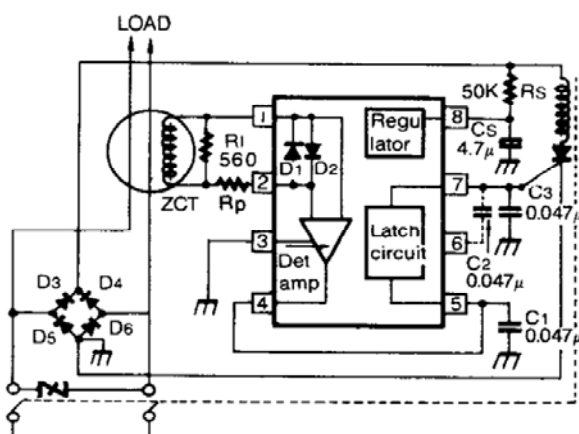


Figure 2. Full-Wave Application Circuit

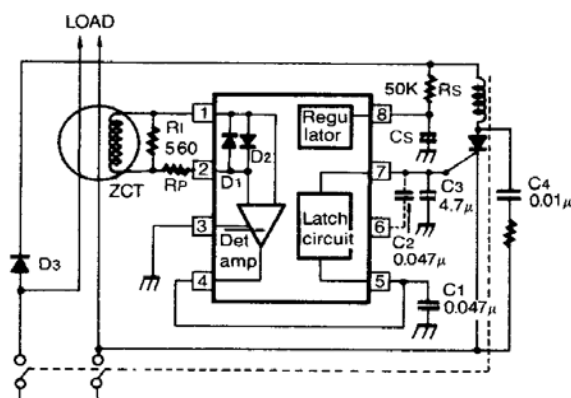


Figure 3. Half-Wave Application Circuit

### Application Information

(Refer to full-wave application circuit in Figure 2)

Figure 2 shows the KA2803B connected in a typical leakage current detector system. The power is applied to the VCC terminal (Pin 8) directly from the power line. The resistor  $R_S$  and capacitor  $C_S$  are chosen so that Pin 8 voltage is at least 12 V. The value of  $C_S$  is recommended above 1  $\mu$ F.

If the leakage current is at the load, it is detected by the zero current transformer (ZCT). The output voltage signal of ZCT is amplified by the differential amplifier of the KA2803B internal circuit and appears as a half-cycle sine wave signal referred to input signal at the output of the amplifier. The amplifier closed-loop gain is fixed about 1000 times with internal feedback resistor to compensate for zero current transformer (ZCT) variations. The resistor  $R_L$  should be selected so that the breaker satisfies the required sensing current. The protection resistor  $R_P$  is not usually used when high current is injected at the breaker; this resistor

should be used to protect the earth leakage detector IC (KA2803B). The range of  $R_P$  is from several hundred  $\Omega$  to several  $k\Omega$ .

Capacitor  $C_1$  is for the noise canceller and a standard value of  $C_1$  is 0.047  $\mu$ F. Capacitor  $C_2$  is also a noise canceller capacitance, but it is not usually used.

When high noise is present, a 0.047  $\mu$ F capacitor may be connected between Pins 6 and 7. The amplified signal finally appears at the Pin 7 with pulse signal through the internal latch circuit of the KA2803B. This signal drives the gate of the external SCR, which energizes the trip coil, which opens the circuit breaker. The trip time of the breaker is determined by capacitor  $C_3$  and the mechanism breaker. This capacitor should be selected under 1  $\mu$ F to satisfy the required trip time. The full-wave bridge supplies power to the KA2803B during both the positive and negative half cycles of the line voltage. This allows the hot and neutral lines to be interchanged.

## ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Min.	Max.	Unit
V <sub>CC</sub>	Supply Voltage		20	V
I <sub>CC</sub>	Supply Current		8	mA
P <sub>D</sub>	Power Dissipation		300	mW
T <sub>L</sub>	Lead Temperature, Soldering 10 Seconds		260	°C
T <sub>A</sub>	Operation Temperature Range	-25	+80	°C
T <sub>STG</sub>	Storage Temperature Range	-65	+150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

## PACKAGE MARKING AND ORDERING INFORMATION

Part Number	Operating Temperature Range	Package	Packing Method
KA2803B	-25 to +80°C	8-Lead, Dual Inline Package (DIP)	Tube
KA2803BD	-25 to +80°C	8-Lead, Small Outline Package (SOP)	Tape and Reel

ELECTRICAL CHARACTERISTICS (T<sub>A</sub> = -25°C to +80°C unless otherwise noted)

Symbol	Parameter	Conditions	Test Circuit	Min.	Typ.	Max.	Units
I <sub>CC</sub>	Supply Current 1	V <sub>CC</sub> = 12V V <sub>R</sub> = OPEN V <sub>I</sub> = 2 V	Figure 4			580	μA
				300	400	530	
						480	
V <sub>T</sub>	Trip Voltage	V <sub>CC</sub> = 16 V, V <sub>R</sub> = 2 V~2.02 V, V <sub>I</sub> = 2	Figure 5	14	16	18	mV (ms)
		Note 1		12.5	14.2	17.0	
I <sub>O(D)</sub>	Differential Amplifier Current Current 1	V <sub>CC</sub> = 16 V, V <sub>R</sub> ~V <sub>I</sub> = 30 mV, V <sub>OD</sub> = 1.2 V	Figure 7	-12	20	-30	μA
	Differential Amplifier Current Current 2	V <sub>CC</sub> = 16 V, V <sub>OD</sub> = 0.8 V, V <sub>R</sub> , V <sub>I</sub> Short = V <sub>P</sub>	Figure 8	17	27	37	
I <sub>O</sub>	Output Current	V <sub>SC</sub> = 1.4 V, V <sub>OS</sub> = 0.8 V, V <sub>CC</sub> = 16.0 V	Figure 9	200	400	800	μA
				200	400	800	
				100	300	600	
V <sub>SCON</sub>	Latch-On Voltage	V <sub>CC</sub> = 16 V	Figure 10	0.7	1.0	1.4	V
I <sub>SCON</sub>	Latch Input Current	V <sub>CC</sub> = 16 V	Figure 11	-13	-7	-1	μA
I <sub>OSL</sub>	Output Low Current	V <sub>CC</sub> = 12 V, V <sub>OSL</sub> = 0.2 V	Figure 12	200	800	1400	μA
V <sub>IDC</sub>	Differential Input Clamp Voltage	V <sub>CC</sub> = 16 V, I <sub>IDC</sub> = 100 mA	Figure 13	0.4	1.2	2.0	V
V <sub>SM</sub>	Maximum Current Voltage	I <sub>SM</sub> = 7 mA	Figure 14	20	24	28	V
I <sub>S2</sub>	Supply Current 2	V <sub>CC</sub> = 12.0 V, V <sub>OSL</sub> = 0.6 V	Figure 15	200	400	900	μA
V <sub>SOFF</sub>	Latch-Off Supply Voltage	V <sub>OS</sub> = 12.0 V	Figure 16	7	8	9	V
		V <sub>SC</sub> = 1.8 V					
		I <sub>IDC</sub> = 100.0 mA					
t <sub>ON</sub>	Response Time	V <sub>CC</sub> = 16 V, V <sub>R</sub> ~V <sub>I</sub> = 0.3 V, 1 V<V <sub>X</sub> <5 V	Figure 17	2	3	4	ms

1. Guaranteed by design, not tested in production.

## TEST CIRCUITS

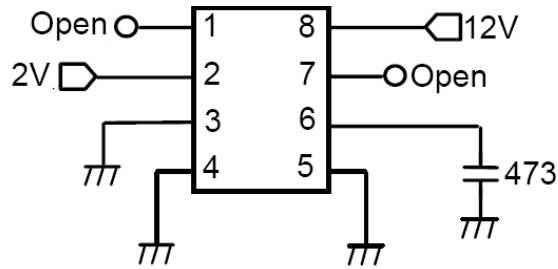


Figure 4. Supply Current 1

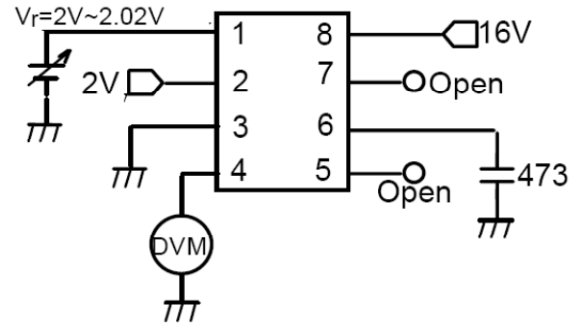


Figure 5. Trip Voltage

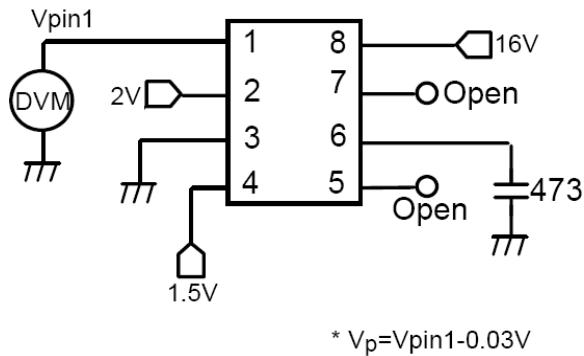
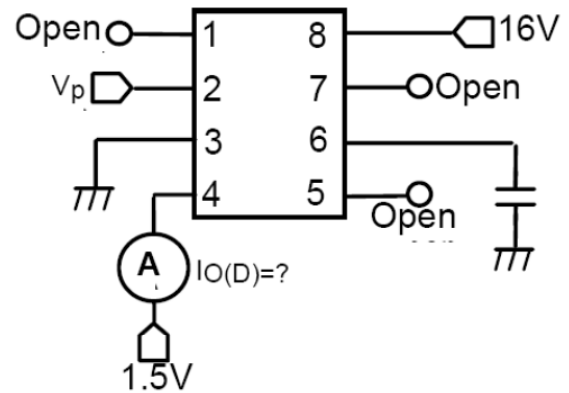
Figure 6.  $V_{PN1}$  for  $V_P$  Measurement

Figure 7. Differential Amplifier Output Current 1

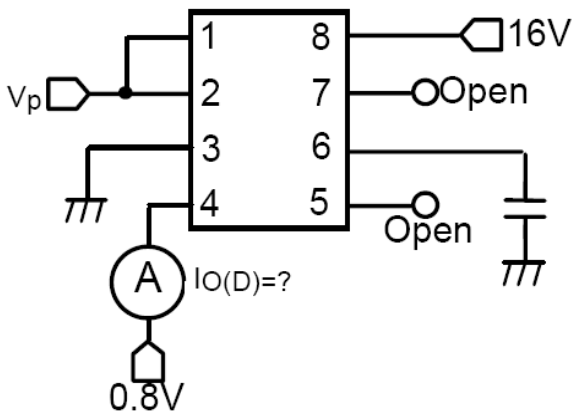


Figure 8. Differential Amplifier Output Current 2

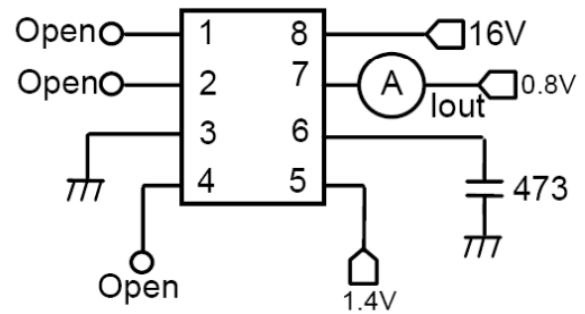


Figure 9. Output Current

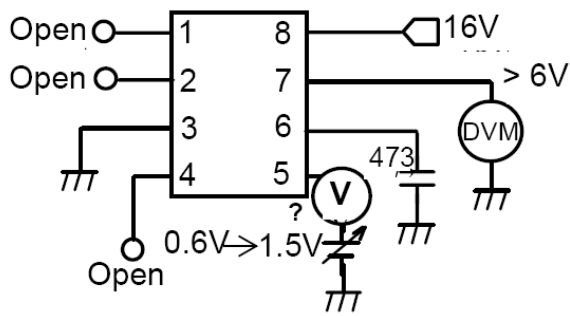


Figure 10. Latch-On Voltage

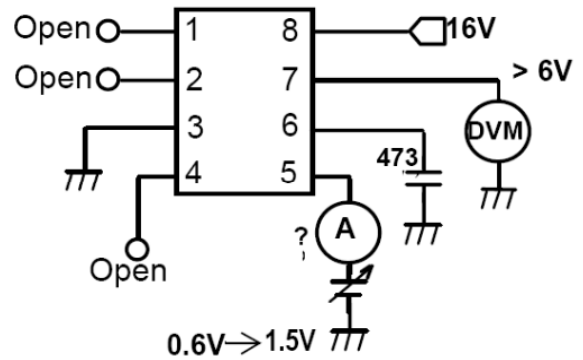


Figure 11. Latch Input Current

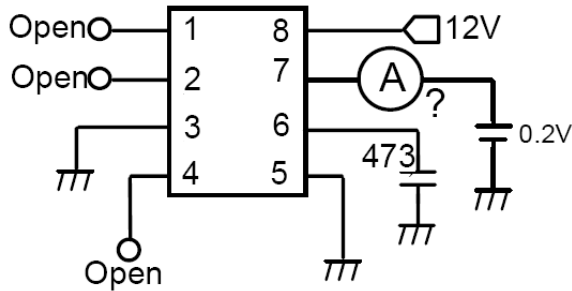


Figure 12. Output Low Current

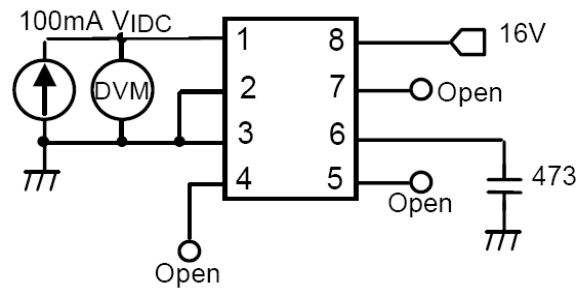


Figure 13. Differential Input Clamp Voltage

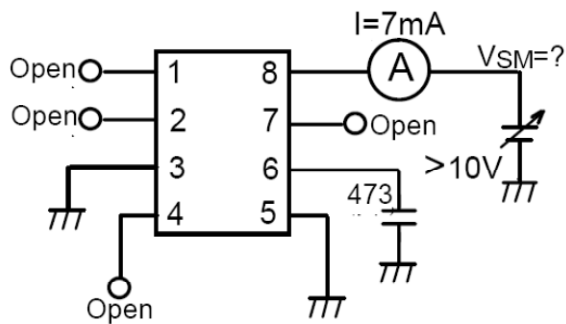


Figure 14. Maximum Current Voltage

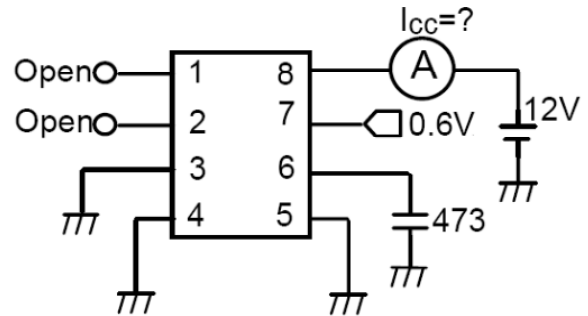


Figure 15. Supply Current 2

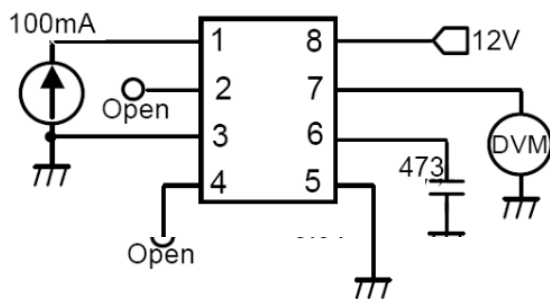


Figure 16. Latch-Off Supply Voltage

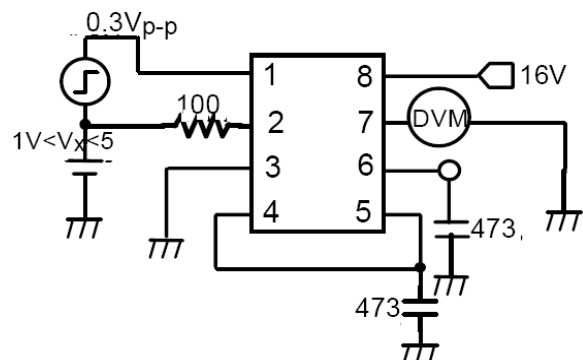


Figure 17. Response Time

## TYPICAL PERFORMANCE CHARACTERISTICS

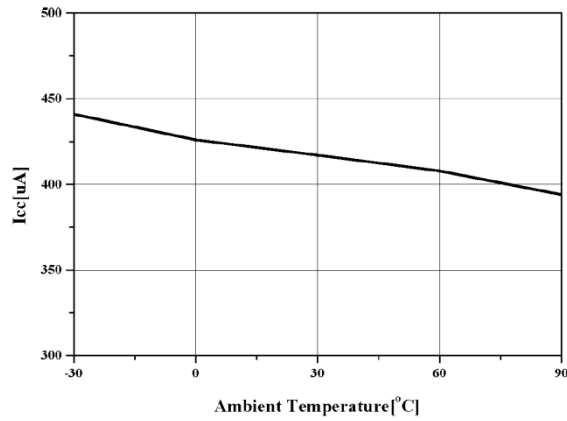


Figure 18. Supply Current

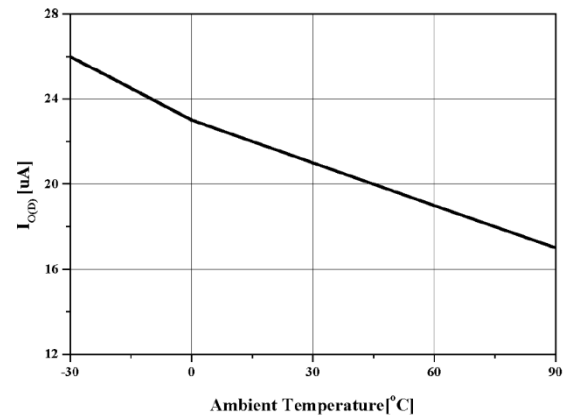
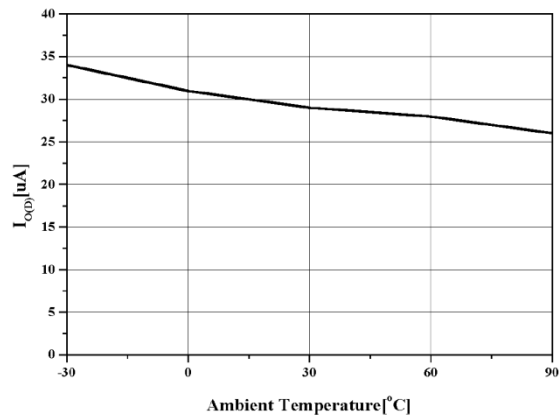
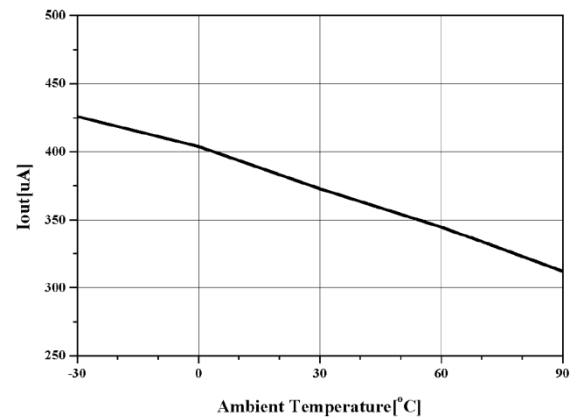
Figure 19. Differential Amplifier Output Current  
( $V_R - V_I = 30 \text{ mV}$ ,  $V_{OD} = 1.2 \text{ V}$ )Figure 20. Differential Amplifier Output Current  
( $V_R, V_I = V_P$ ,  $V_{OD} = 0.8 \text{ V}$ )

Figure 21. Output Current

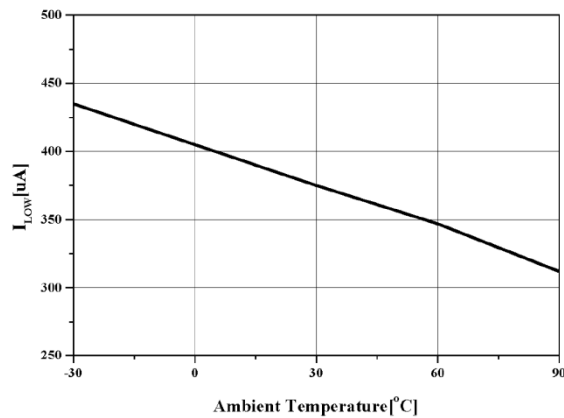
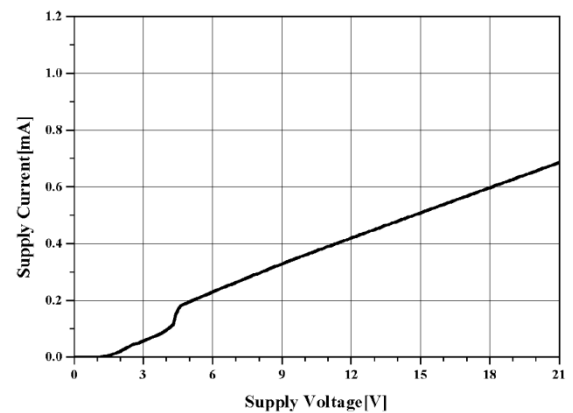


Figure 22. Output Low Current

Figure 23.  $V_{CC}$  Voltage vs. Supply Current 1

## TYPICAL PERFORMANCE CHARACTERISTICS (continued)

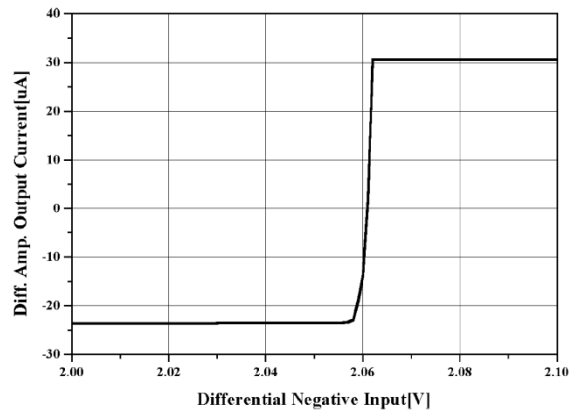


Figure 24. Differential Amplifier Output Current 1

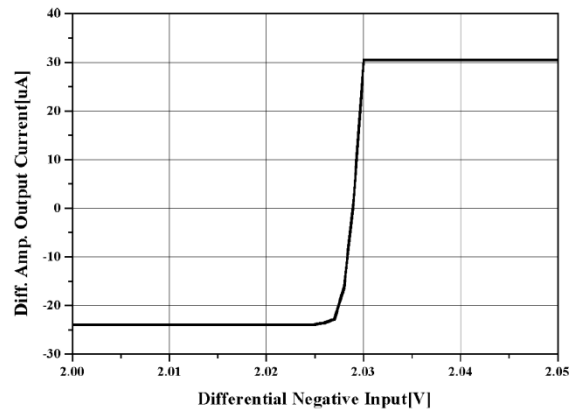


Figure 25. Differential Amplifier Output

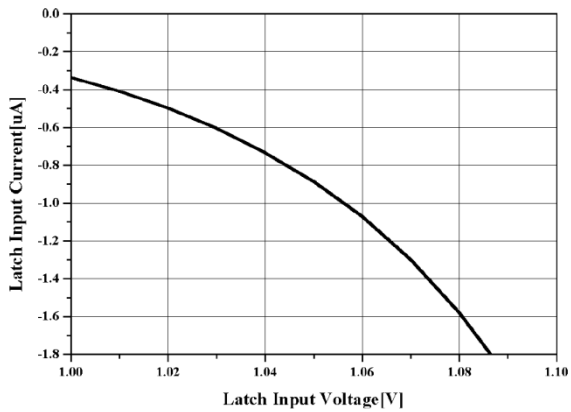


Figure 26. Latch Input Current

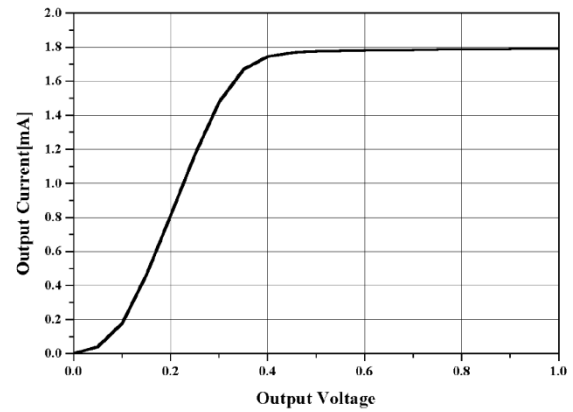


Figure 27. Output Low Current

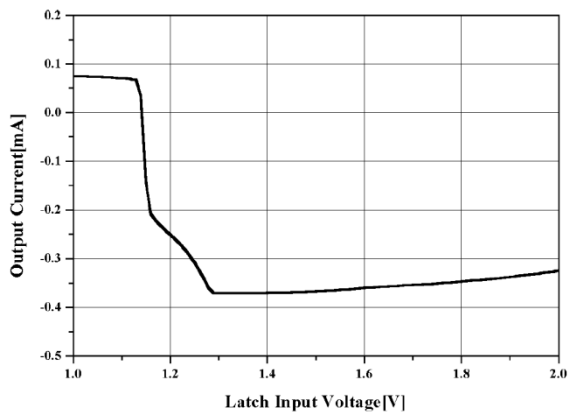
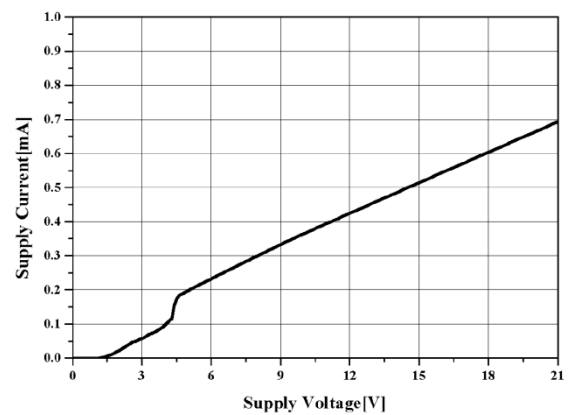


Figure 28. Output Current

Figure 29.  $V_{CC}$  Voltage vs. Supply Current 2

## TYPICAL PERFORMANCE CHARACTERISTICS (continued)

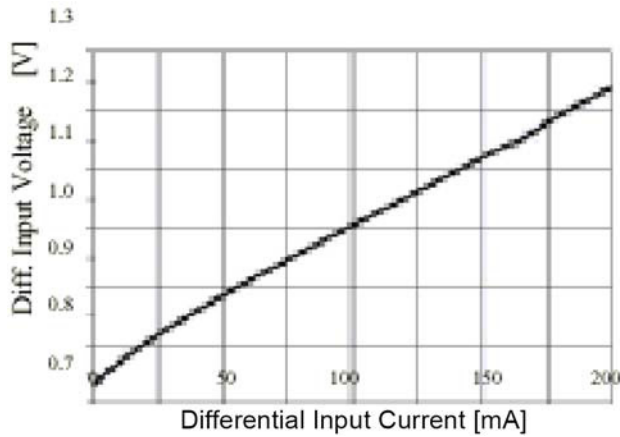


Figure 30. Differential Input Clamp Voltage

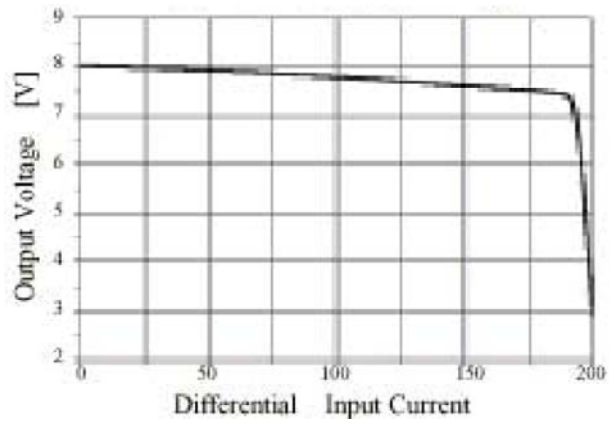


Figure 31. Latch-Off Supply Voltage

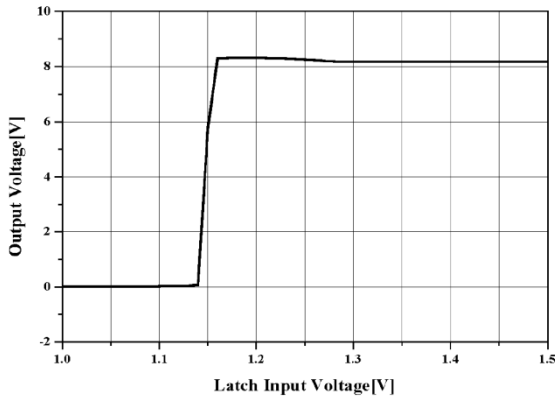


Figure 32. Latch-On Input Voltage

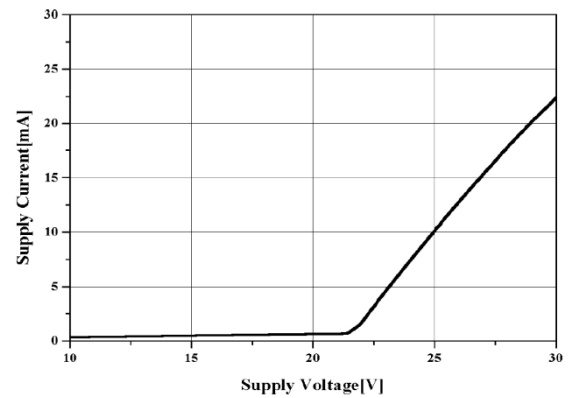


Figure 33. Maximum Supply

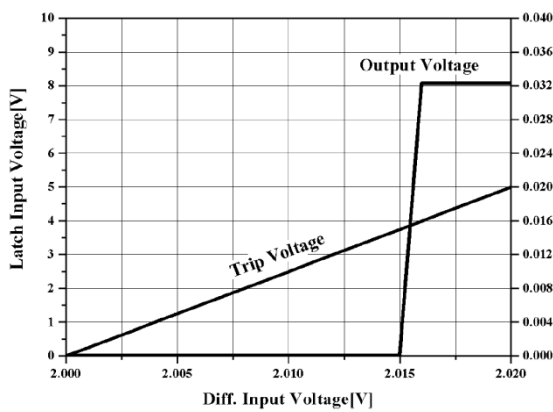


Figure 34. Trip and Output

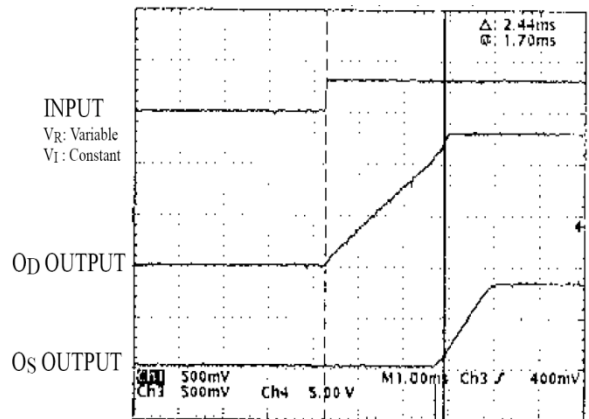


Figure 35. Output Response Time

# MECHANICAL CASE OUTLINE

## PACKAGE DIMENSIONS

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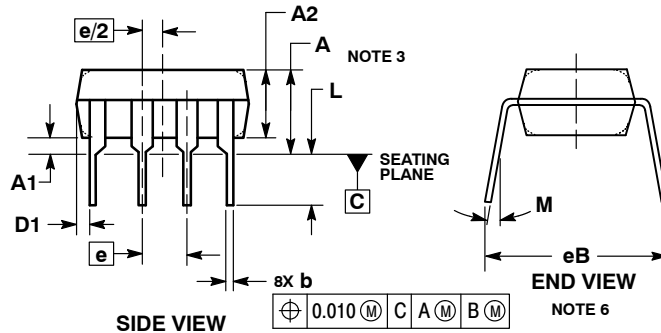
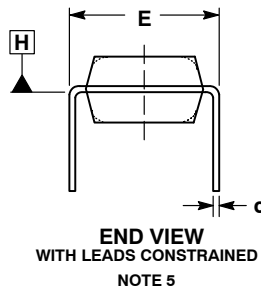
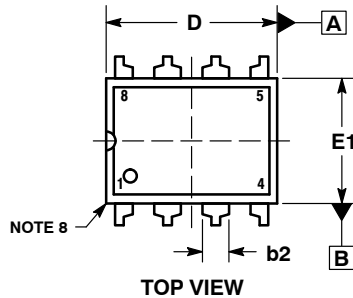
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SCALE 1:1

PDIP-8  
CASE 626-05  
ISSUE P

DATE 22 APR 2015

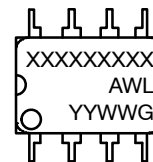


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3. DIMENSIONS A, A1 AND L ARE MEASURED WITH THE PACKAGE SEATED IN JEDEC SEATING PLANE GAUGE GS-3.
4. DIMENSIONS D, D1 AND E1 DO NOT INCLUDE MOLD FLASH OR PROTRUSIONS. MOLD FLASH OR PROTRUSIONS ARE NOT TO EXCEED 0.10 INCH.
5. DIMENSION E IS MEASURED AT A POINT 0.015 BELOW DATUM PLANE H WITH THE LEADS CONSTRAINED PERPENDICULAR TO DATUM C.
6. DIMENSION eB IS MEASURED AT THE LEAD TIPS WITH THE LEADS UNCONSTRAINED.
7. DATUM PLANE H IS COINCIDENT WITH THE BOTTOM OF THE LEADS, WHERE THE LEADS EXIT THE BODY.
8. PACKAGE CONTOUR IS OPTIONAL (ROUNDED OR SQUARE CORNERS).

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	---	0.210	---	5.33
A1	0.015	---	0.38	---
A2	0.115	0.195	2.92	4.95
b	0.014	0.022	0.35	0.56
b2	0.060 TYP		1.52 TYP	
C	0.008	0.014	0.20	0.36
D	0.355	0.400	9.02	10.16
D1	0.005	---	0.13	---
E	0.300	0.325	7.62	8.26
E1	0.240	0.280	6.10	7.11
e	0.100 BSC		2.54 BSC	
eB	---	0.430	---	10.92
L	0.115	0.150	2.92	3.81
M	---	10°	---	10°

### GENERIC MARKING DIAGRAM\*




XXXX = Specific Device Code  
A = Assembly Location  
WL = Wafer Lot  
YY = Year  
WW = Work Week  
G = Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present.

### STYLE 1:

- PIN 1: AC IN  
2. DC + IN  
3. DC - IN  
4. AC IN  
5. GROUND  
6. OUTPUT  
7. AUXILIARY  
8. V<sub>CC</sub>

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# MECHANICAL CASE OUTLINE

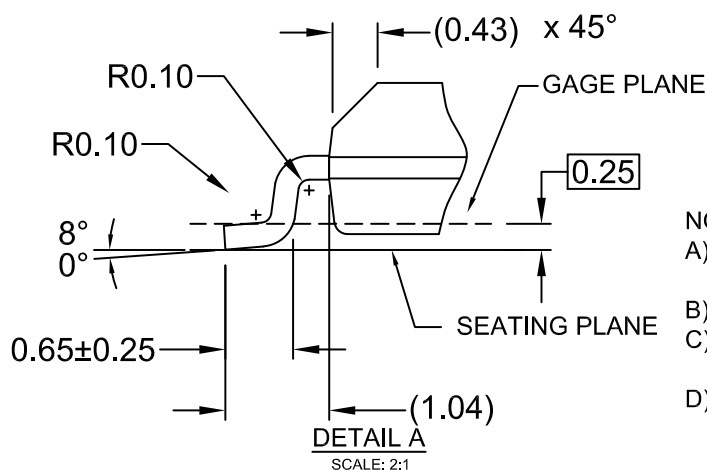
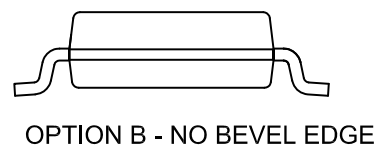
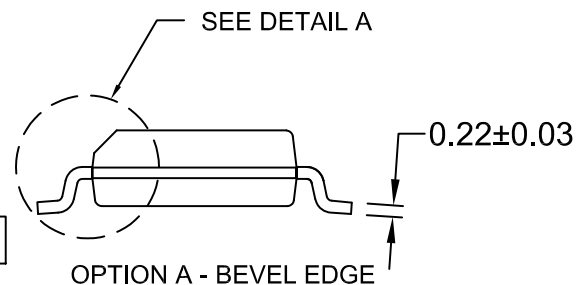
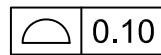
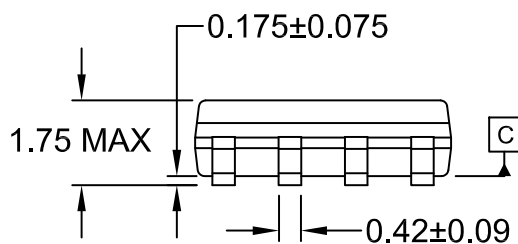
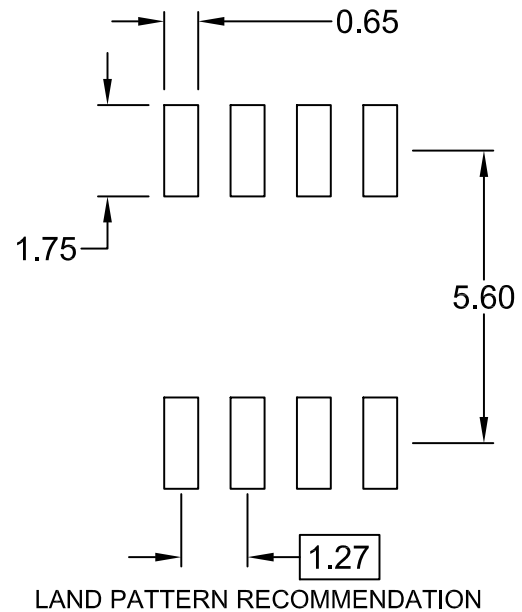
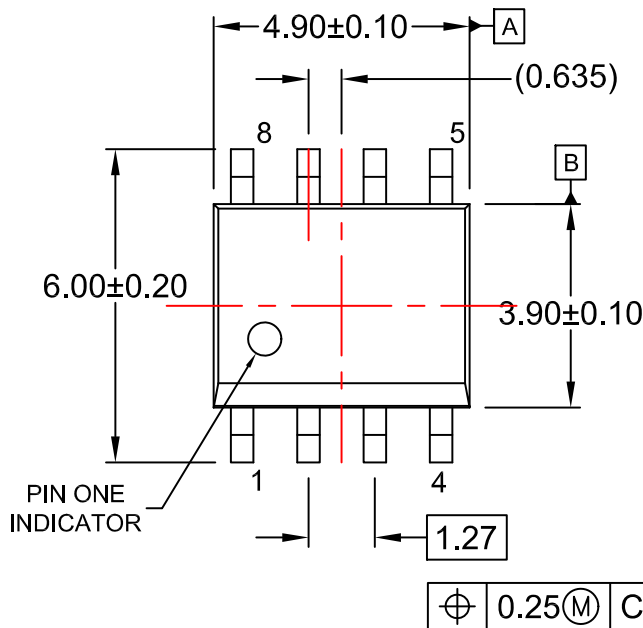
## PACKAGE DIMENSIONS

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ON

SOIC8  
CASE 751EB  
ISSUE A

DATE 24 AUG 2017



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- D) LANDPATTERN STANDARD: SOIC127P600X175-8M

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